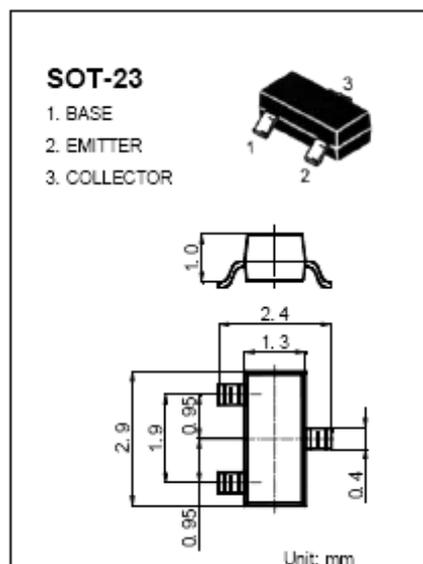


FEATURES

- Power dissipation, P_{CM} : 0.2W ($T_{amb}=25^{\circ}C$)
- Collector current, I_{CM} : 0.2A
- Collector-base voltage, $V_{(BR)CBO}$: 60V
- Operating and storage junction temperature range:
 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$
- SOT-23 plastic-encapsulate package

Device Marking: AM1



ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$		40	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 60V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 40V, I_B = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = 10V, I_C = 1mA$		100	
	$H_{FE(2)}$	$V_{CE} = 1V, I_C = 50mA$	60	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50mA, I_B = 5mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50mA, I_B = 5mA$		0.95	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 10mA$ $f = 100MHz$	250		MHz
Delay Time	t_d	$V_{CC} = 3.0V_{dc}, V_{BE} = 0.5V_{dc}$		35	nS
Rise Time	t_r	$I_C = 10mA_{dc}, I_B1 = 1.0mA_{dc}$		35	nS
Storage Time	t_s	$V_{CC} = 3.0V_{dc}, I_C = 10mA_{dc}$		200	nS
Fall Time	t_f	$I_B1 = I_B2 = 1.0mA_{dc}$		50	nS

Note: Unless otherwise specified, these specifications apply over the operating ambient temperature of $25^{\circ}C$.

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